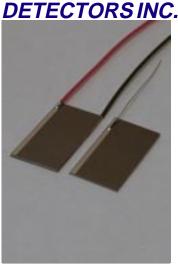
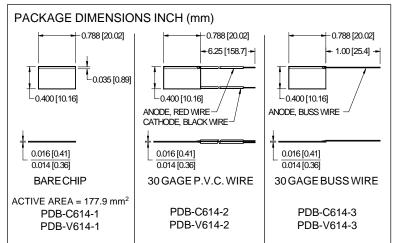
PHOTONIC Silicon Photodiode, Blue Enhanced Solderable Chips

Photoconductive Type PDB-C614 Photovoltaic Type PDB-V614





FEATURES

- Blue enhanced
- Photovoltaic type
- Photoconductive type
- High quantum efficiency

DESCRIPTION: Low cost blue enhanced planar diffused silicon solderable photodiode. The **PDB-V614** cell is designed

for low noise, photovoltaic applications. The **PDB-C614** cell is designed for low capacitance, high speed, photoconductive

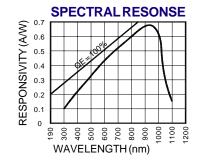
operation. They are available bare, PVC or buss wire leads.

APPLICATIONS

- Optical encoder
- Position sensor
- Industrial controls
- Instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER .	PDB-	C614	PDB-	V614	UNITS
OTWIDGE		MIN	MAX	MIN	MAX	Oraro
VBR	Reverse Voltage		75		25	V
T _{STG}	Storage Temperature	-40	+125	-40	+125	°C
To	Operating Temperature Range	-40	+100	-40	+100	∘C
Ts	Soldering Temperature		+224		+224	°C
I _L	Light Current		500		500	mA



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	PDB-C614			PDB-V614			LINITO
			MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current	H = 100 fc, 2850 K	1.89	2.10		1.89	2.10		mA
ΙD	Dark Current	H = 0, V _R = 5 V*		250	500	100	500		nA
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	.25	.5		.5	1		MΩ
TC RsH	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8			-8		%/°C
Сл	Junction Capacitance	H = 0, V _R = 5 V**		750			21000		pF
λrange	Spectral Application Range	Spot Scan	350		1100	350		1100	nm
λр	Spectral Response - Peak	Spot Scan		940			940		nm
V _{BR}	Breakdown Voltage	I = 10 μA	25	50		5	15		V
NEP	Noise Equivalent Power	V _R = 0 V @ Peak	1.4 x 10 ⁻¹² TYP		2 x 10 ⁻¹³ TYP		W/ √Hz		
tr	Response Time	RL = 1 KΩ V _R = 5 V**		125			6500		nS